

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	3176	(257/328-334).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/13 16:25
S12	3273	(257/328-334).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/13 16:25
S13	103	S12 and (@pd>="20060901")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 18:10
S2	2758	S1 and (@ad<="20030724" or @rlad<="20030724")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 18:11
S15	620	S14 and (@ad<="20030724" or @rlad<="20030724")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/13 18:11
S11	32	(drift and buried and gate and channel and semiconductor).clm.	US-PGPUB	OR	ON	2006/12/14 14:04
S14	741	"vertical field effect transistor" or (vertical adj field adj effect adj trnasistor) or (vertical adj junction adj field adj effect adj trnasistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 14:05

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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	32	(drift and buried and gate and channel and semiconductor).clm.	US-PGPUB	OR	ON	2006/12/14 14:04
L4	128	("vertical field effect transistor" or (vertical adj field adj effect adj trnasistor) or (vertical adj junction adj field adj effect adj trnasistor)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 14:05